

Form PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5649-805DV		Serial No. To Be Assigned	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Kang-Wook Park		GAU:	
				Filing Date: Concurrently Herewith			
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Examiner Initials	Document No.	Date	Name	Class	Subclass	Filing Date if Appropriate	
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DF	27	Ugajin et al., Very-High f_j and f_{max} Silicon Bipolar Transistors Using Ultra-High-Performance Super Self-Aligned Process Technology for Low-Energy and Ultra-High-Speed LSI's, IEDM, 1995, pp. 735-738					
DF	28	Wolf, S., Silicon Processing for the VLSI Era Volume 2: Process Integration, Sunset Beach, CA, 1990, pp. 52, 510-512					
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